

MANUFACTURE OF SILICON WAFER

Title:

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Equivalents:

Abstract

PURPOSE: To provide a method of manufacturing a silicon wafer which is lessened in BMD density in an LSI device thermal treatment, wherein a trouble that BMD is excessively produced is solved by a conventional PBS technique.

CONSTITUTION: Single crystal silicon grown through a CZ method is formed into a silicon wafer possessed of a polycrystalline silicon film on its rear surface in a silicon wafer manufacturing process, wherein a thermal treatment is carried out in an oxidizing atmosphere or a non-oxidizing atmosphere at a temperature range of 800 to 1100 deg.C for 30 to 120 minutes before a polycrystalline silicon film growth process is performed.